

Supporting Information

“Resistive Switching Characteristics of Li-doped ZnO Thin Films based on Magnetron Sputtering”

1. Multiple I - V characteristics of the resulted devices under a DC voltage.

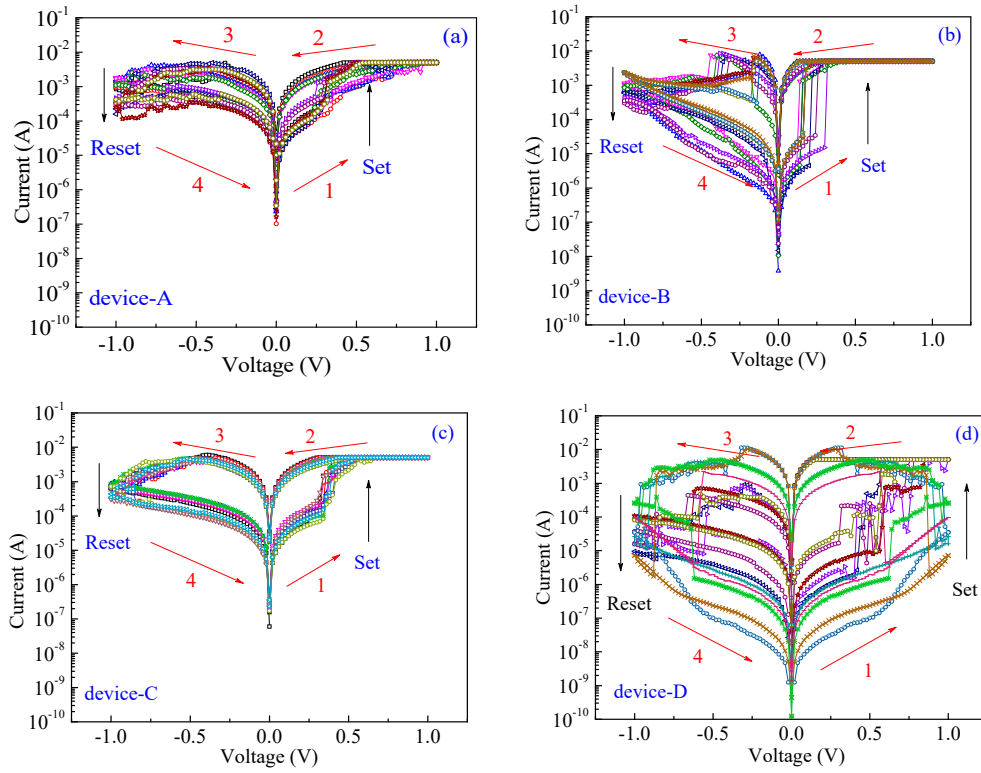


Figure S1. The I - V characteristics: (a) device-A; (b) device-B; (c) device-C; (d) device-D.

2. The curves of cumulative distributions and the coefficient of variation (σ/μ) of R_{LRS} and R_{HRS}

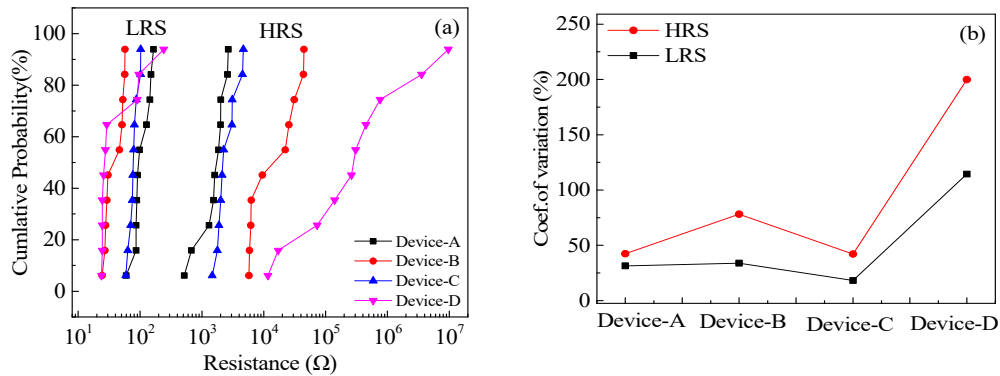


Figure S2. (a) The cumulative distributions of R_{LRS} and R_{HRS} ; (b) The coefficient of

variation of R_{LRS} and R_{HRS} distribution.

3. The endurance characteristics of resistive switching device.

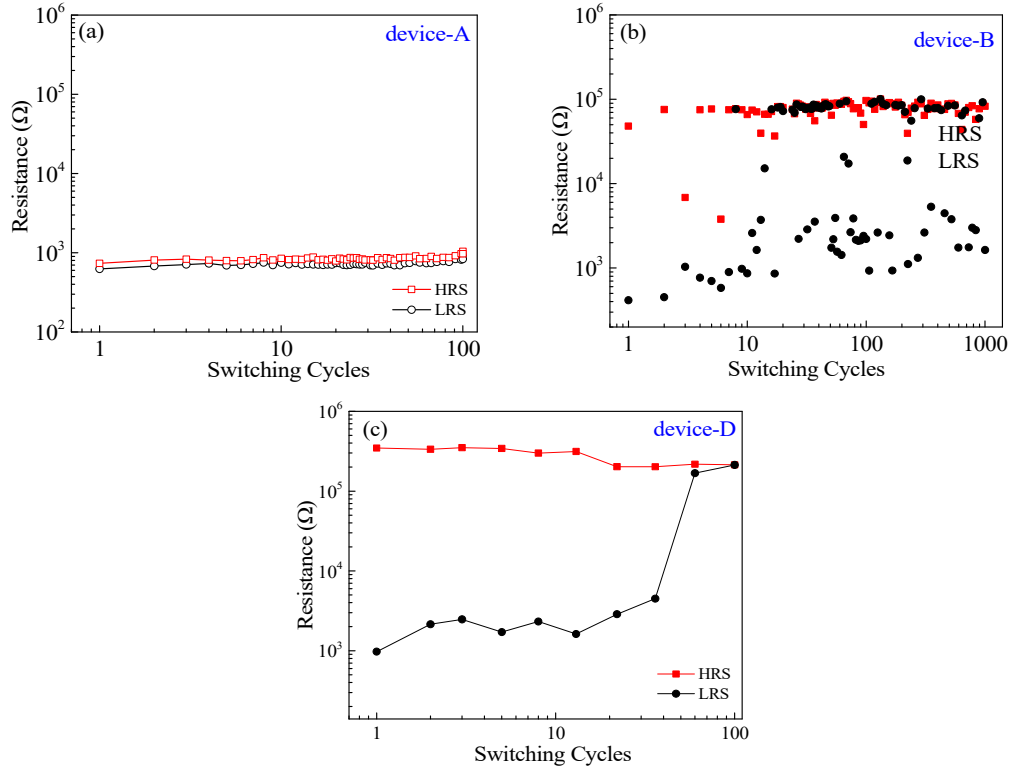


Figure S3. The endurance performances of (a) device-A; (b) device-B; (c) device-D.